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(54) **Title**: PHOTORESIST RESIDUE AND POLYMER RESIDUE REMOVING LIQUID COMPOSITION

(54) 発明の名称 : フォトレジスト残渣およびポリマー残渣除去液組成物

[図1]

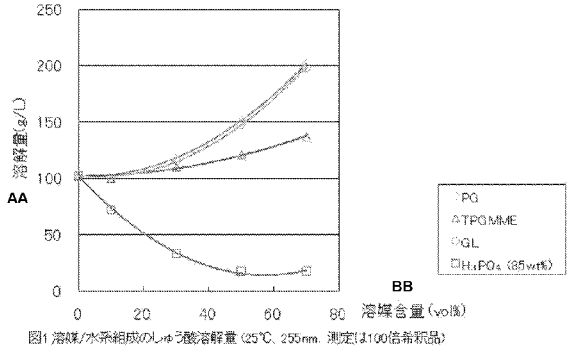


図1 溶媒/水系組成のしゅう酸溶解量 (25℃、255nm. 測定は100倍希釈品)

CC

AA AMOUNT OF DISSOLUTION (g/L)
BB AMOUNT OF SOLVENT (VOL.%)
CC FIG. 1: AMOUNT OF OXALIC ACID DISSOLUTION OF SOLVENT/AQEUOUS COMPOSITION (25 °C, 255 nm; MEASUREMENT IS 100 TIMES DILUENT)

(57) **Abstract**: Provided are a photoresist residue and polymer residue removing liquid composition, and a method of removing the residue used therewith, for removing photoresist residue and polymer residue produced during a process of manufacturing a semiconductor circuit element having metallic wiring. Specifically, the composition does not contain nitrogen-containing organic hydroxyl compounds, ammonia or fluorine compounds, and contains an aliphatic polycarboxylic acid having a melting point of 25 °C or higher with an excellent residue removing property and having a metallic oxide main component as the residue removing component. The photoresist residue and polymer residue removing liquid composition, and the method of removing the residue used therewith, is capable of preventing the aliphatic polycarboxylic acid from being recrystallized by evaporation of water after a solution has adhered around a cleaning device liquid ejecting nozzle or a cleaning tank and a chamber. In the photoresist residue and polymer residue removing liquid composition containing the aliphatic polycarboxylic acid with a melting point of 25 °C or higher, the removing liquid contains an organic solvent that is miscible with water and has a vapor pressure of 17 mm Hg or less at 20 °C and a hydroxyl group within the structure.

(57) 要約:

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